

ABSTRACT OF THE DISCLOSURE:

An TMR-type MRAM comprising a transistor for selection; a first connecting hole; a first wiring (write-in word line); a second insulating interlayer covering a first insulating interlayer and the first wiring; a TRM device formed on the second insulating interlayer; a second wiring (bit line) formed on a third insulating interlayer; and a second connecting hole formed through the second insulating interlayer and connected to the first connecting hole, in which an end face of an extending portion of the other end of the TRM device is in contact with the second connecting hole.